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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/625,451	07/23/2003	Jan Raebiger	2000.108200	7974	
23720 75	90 12/27/2004		EXAM	EXAMINER	
WILLIAMS, MORGAN & AMERSON, P.C.			MATHEWS	MATHEWS, ALAN A	
HOUSTON, TX	MOND, SUITE 1100 TX 77042		ART UNIT	PAPER NUMBER	
•			2851		
			DATE MAILED: 12/27/2004	DATE MAILED: 12/27/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

		16r
	Application No.	Applicant(s)
	10/625,451	RAEBIGER ET AL.
Office Action Summary	Examiner	Art Unit
	Alan A. Mathews	2851
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).
Status		
1) ☐ Responsive to communication(s) filed on  2a) ☐ This action is FINAL. 2b) ☑ This  3) ☐ Since this application is in condition for allowar closed in accordance with the practice under E	action is non-final. nce except for formal matters, pro	
Disposition of Claims		
4) Claim(s) <u>1-26</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) □ Claim(s) is/are allowed. 6) □ Claim(s) <u>1-26</u> is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and/or	vn from consideration.	
Application Papers		
9) ☐ The specification is objected to by the Examine 10) ☒ The drawing(s) filed on 13 July 2003 is/are: a) Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	☑ accepted or b)☐ objected to be drawing(s) be held in abeyance. See ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Application of the contraction of the contr	ion No ed in this National Stage
Attachment(s)		
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)         Paper No(s)/Mail Date <u>7-15-04</u>.     </li> </ol>	4) Interview Summary Paper No(s)/Mail D  5) Notice of Informal F  6) Other:	•

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

- (a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.
- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1-4, 6, 7, 13 16, 20, and 26 are rejected under 35 U.S.C. 102(a) as being anticipated by Bode et al. (U. S. Patent Application Publication No. 2002,0106821 A1, cited on Applicant's PTO-1449). Bode et al. discloses in figures 2 and 3 and pages 3 and 4, paragraphs # 31-35, a method of determining the exposure dose (exposure parameter) for a multi-step exposure process in a semi conductor line. Paragraph # 34 further discloses measuring the thickness of the layers of photoresist at various locations across the surface of wafer 21, which is the step of obtaining information about an inline parameter (layer thickness) indicative of a characteristic of a predefined location on a substrate (wafer). The controller 38 then determines, based upon the measurement data by metrology tool 29, the exposure dose in the stepper 30, which is the step of updating at least one exposure parameter (exposure dose) for said predefined location on the basis of said information. Step 37 in figure 4 and paragraph # 35 disclose that the exposure process is comprised of across wafer variation in exposure dose in response to the thickness measurements. With respect to claim 4, figure 3 discloses measurement data by

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metrology tool 29 occurring prior to exposing the substrate by stepper 30. With respect to claim 6, paragraph # 34 states "The measurement data provided to the controller 38 may be averaged or otherwise statistically manipulated in the controller 38". With respect to claim 13, the "target offset" is just the difference of the exposure parameter (exposure dose) that is adjusted as a result of the measurement data. With respect to claim 14, paragraph # 35 discloses measuring the thickness 26 of the layer of photoresist 25. In addition, paragraph # 10 discloses variations in the topology of one or more of the underlying films in process layers. With respect to claim 15, paragraph # 28 recites using a mask. Paragraph # 28 also recites forming a layer of photoresist material above a process layer, which would be the step of preparing said substrates for receiving a resist mask. The exposure map would be the exposure dose, which is based on location within the substrate.

Claims 1-3, 5, 13 – 15, 17, 19, 23, 24, and 26 are rejected under 35 U.S.C. 102(b) as being anticipated by Miller et al. (U. S. Patent No. 6,259,5210). Miller et al. discloses in figures 2 and 3 and column 3, lines 10-67, a scatterometer 140 that obtains information about an inline parameter (intensity of the reflected light from the wafer). Column 4, lines 8-17, discloses changing the recipe of the stepper which is updating the exposure parameter (exposure energy or duration of exposure) based on the information. With respect to claims 5 and 23, figure 2 discloses that the measurement from the scatterometer 140 occurs after exposure in stepper 110. With respect to claim 13, the "target offset" is just the difference of the exposure parameter (exposure energy or duration) that is adjusted as a result of the measurement data. With respect to claim 14, column 3, lines 66 and 67, and column 4, lines 1-7, disclose measuring a variation in

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the line widths of the baked region, which would by a topography of the substrate. With respect to claim 15, preparing the substrate for receiving a resist mask would be forming a resist layer on the wafer (see claim 1 of Miller et al.). Establishing an exposure map would be the exposure recipe for the stepper. Column 3, lines 27-29, disclose adjusting the recipe of the stepper 110 based on the wafer measurements. This is updating the exposure map for a plurality of specified locations (such as in the middle and the periphery, see column 3, line 66). Exposing the substrate would be done by stepper 110.

4. Claims 1–26 are rejected under 35 U.S.C. 102(b) as being anticipated by Park U. S. Patent Application Publication No. 2002/0001070, cited in Applicant's PTO-1449). Park discloses in figure 1 and paragraph # 35, 36, and 40, an after development inspection (ADI) process 30 (after exposure) for obtaining information about an inline parameter (line width). Paragraphs # 44 and 61 disclose updating an exposure parameter (exposure time) on the basis of process 30. With respect to claim 4, paragraph # 54 and 56 further disclose that the pre-exposure step process 10 should help determine the photo-exposure time. Note that a sentence in paragraph # 56 states "Also, the thickness of the silicone-nitride film, which has been formed in a pre-exposure step process of each prior task, is inspected, as are the line widths obtained from ADI when a desired photo-exposure time is used in the photo-exposure process". Thus, both pre-exposure and post-exposure measurements are taken to determine the photo-exposure time. With respect to claim 8, the plurality of inline parameters would be both the thickness of the film and line widths. With respect to claim 6, paragraph # 45, 48, and 63 disclose averaging. With respect to claim 13, the target offset is the change in exposure time

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ΔET (based on the measurements). With respect to claim 15, the pre-exposure step 10 includes depositing silicon-nitride film on the surface of a wafer, which would be the step of preparing the substrate.

5. Claims 1, 3, 5, 6, 7, 13 – 15, 17, 19, 23, 24, and 26 are rejected under 35 U.S.C. 102(b) as being anticipated by Luhn U. S. Patent Application Publication No. 2002/0012861, cited on Applicant's PTO-1449). Luhn et al. discloses in figure 2 and paragraphs # 60-66, obtaining information (measuring) about an inline parameter (line width or positional errors). Corrections for the exposure dose or intensity E and the xy positioning are then calculated, which would be the updating of at least one exposure parameter (exposure intensity E). With respect to claim 6, the last three lines of paragraph # 60 and the last three lines of paragraph # 62 disclose averaging the line width. With respect to claim 13, the correction values for exposure intensity E would be the target offset. With respect to claim 14, the line width would be the topography of the substrate. With respect to claim 15, lines 1-7 of paragraph # 60 disclose establishing an exposure map for a step and repeat (photostepper) exposure of the substrate. The preparing of the substrates would be placing a photoresist layer on the substrate.

## Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The patents on Applicant's PTO 1449 are cited for the same reasons Applicant cited them in his INFORMATION DISCLOSURE STATEMENT.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alan A. Mathews whose telephone number is (571) 272-2123. The examiner can normally be reached on Monday through Friday from 8:00 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Judy Nguyen can be reached on (571) 272-2258. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Alan A. Mathews Primary Examiner

Olan a. Mathen

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